AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A material for forming copper undercoat films comprising a compound represented by the general formula

$$(R_1R_2)P\text{-}(R)n\text{-}Si\ (X_1X_2X_3)$$

wherein at least one of X_1, X_2 and X_3 is a hydrolytic group, R_1 and R_2 are alkyl groups, R denotes a chain-form organic group formed from alkyl groups, aromatic rings or alkyl groups containing aromatic rings, and n is an integer from 1 to 6, wherein the material prevents copper diffusion.

2. (Currently Amended) A material for forming copper undercoat films comprising a compound represented by the general formula:

$$(R_1R_2)P\text{-}(R)n\text{-}Si\ (X_1X_2X_3)$$

wherein at least one of X_1, X_2 and X_3 is selected from a group comprising halogens, alkoxide groups, amino groups and isocyanate groups, R_1 and R_2 are alkyl groups with carbon numbers of 1-21, R has a carbon number of 1-50, and denotes a chain-form organic group formed from alkyl groups, aromatic rings or alkyl groups containing aromatic rings, and n is an integer from 1 to 6, wherein the material prevents copper diffusion.

3. (Currently Amended) The material for forming copper undercoat films according to claim 1, wherein ~~characterized by the bonding of~~ $(R_1R_2)P\text{-}(R)n\text{-}Si$ groups are bonded to a substrate via Si-O bonding, by a solvent and by the compound represented by the general formula.

4. (Currently Amended) The material for forming copper undercoat films according to claim 1, characterized in that the compound represented by the general formula is selected from the group consisting of: ~~1-dimethylphosphino-2-triethoxysilylethane,~~ 1-diethylphosphino-2-

triethoxysilylethane, 1-diphenylphosphino-2-triethoxysilylethane, 1-dimethylphosphino-2-trimethoxysilylethane, 1-diethylphosphino-2trimethoxysilylethane, 1-diphenylphosphino-2-trimethoxysilylethane, 1-dimethylphosphino-3triethoxysilylpropane, 1-diethylphosphino-3-triethoxysilylpropane, 1-diphenylphosphino-3-triethoxysilylpropane, 1-diphenylphosphino-2-trichlorosilylethane, 1-diphenylphosphino-2trisdimethylaminosilylethane, 1-diphenylphosphino-2-triisocyanatosilylethane and 1-diphenylphosphino-4-triethoxysilylethylbenzene.

5. (Currently Amended) A method ~~The material~~ for forming copper undercoat films comprising~~according to claim 1~~, contacting~~characterized in that~~ the material for forming copper undercoat films of claim 1 ~~is brought into contact~~ with a substrate surface, thus forming a copper undercoat film.

6. (Currently Amended) The method~~material~~ for forming copper undercoat films according to claim 5, wherein the undercoat film is produced by the bonding of $(R_1R_2)P\text{-}(R)_n\text{-}Si$ groups to the substrate via Si-O bonding, and wherein the reaction between $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface occurs in liquid phase.

7. (Currently Amended) The method~~material~~ for forming copper undercoat films according to claim 5, wherein the undercoat film is produced by the bonding of $(R_1R_2)P\text{-}(R)_n\text{-}Si$ groups to the substrate via Si- O bonding, and wherein the reaction between–Si $(X_1X_2X_3)$ groups and -OH groups at the substrate surface occurs in gas phase.

8. (Currently Amended) The method~~material~~ for forming copper undercoat films according to claim 5, wherein the undercoat film is produced by the bonding of $(R_1R_2)\text{-}(R)_n\text{-}Si$ groups to the substrate via Si-O bonding, and wherein the reaction between $-Si(X_1X_2X_3)$ groups and -OH groups at the substrate surface occurs in a supercritical liquid.

9. (Currently Amended) The method~~material~~ for forming copper undercoat films according to claim 5, characterized in that the reaction between -Si($X_1X_2X_3$) groups and -OH groups at the substrate surface is carried out under the condition of room temperature to 450 °C.

10. (Currently Amended) The material for forming copper undercoat films according to claim 2, wherein ~~characterized by the bonding of~~ (R_1R_2)P-(R)n-Si groups are bonded to a substrate via Si-O bonding, by a solvent and by the compound represented by the general formula.

11. (Currently Amended) The material for forming copper undercoat films according to claim 2, characterized in that the compound represented by the general formula is selected from the group consisting of: ~~1-dimethylphosphino-2-triethoxysilylethane,~~ 1-diethylphosphino-2-triethoxysilylethane, 1-diphenylphosphino-2-triethoxysilylethane, 1-dimethylphosphino-2-trimethoxysilylethane, 1-diethylphosphino-2trimethoxysilylethane, 1-diphenylphosphino-2-trimethoxysilylethane, 1-dimethylphosphino-3triethoxysilylpropane, 1-diethylphosphino-3-triethoxysilylpropane, 1-diphenylphosphino-3-triethoxysilylpropane, 1-diphenylphosphino-2-trichlorosilylethane, 1-diphenylphosphino-2trisdimethylaminosilylethane, 1-diphenylphosphino-2-triisocyanatosilylethane and 1-diphenylphosphino-4-triethoxysilylethylbenzene.

12. (Currently Amended) A method ~~The material~~ for forming copper undercoat films comprising~~according to claim 2~~, contacting~~characterized in that~~ the material for forming copper undercoat films of claim 2 ~~is brought into contact~~ with a substrate surface, thus forming a copper undercoat film.

13. (Currently Amended) The method~~material~~ for forming copper undercoat films according to claim 12, wherein the undercoat film is produced by the bonding of (R_1R_2)P-($R)_n$-Si groups to

the substrate via Si-O bonding, and wherein the reaction between -Si($X_1X_2X_3$) groups and -OH groups at the substrate surface occurs in liquid phase.

14. (Currently Amended) The method~~material~~ for forming copper undercoat films according to claim 12, wherein the undercoat film is produced by the bonding of (R_1R_2)P-(R)$_n$-Si groups to the substrate via Si-0 bonding, and wherein the reaction between–Si ($X_1X_2X_3$) groups and -OH groups at the substrate surface occurs in gas phase.

15. (Currently Amended) The method~~material~~ for forming copper undercoat films according to claim 12, wherein the undercoat film is produced by the bonding of (R_1R_2)-(R)$_n$-Si groups to the substrate via Si-O bonding, and wherein the reaction between -Si($X_1X_2X_3$) groups and -OH groups at the substrate surface occurs in a supercritical liquid.

16. (Currently Amended) The method~~material~~ for forming copper undercoat films according to claim 12, characterized in that the reaction between -Si($X_1X_2X_3$) groups and -OH groups at the substrate surface is carried out under the condition of room temperature to 450 °C.